

IN THE CLAIMS:

Please amend claims 1 and 16 as follows. A detailed listing of all claims is as follows.

Claim 1 (Currently Amended): A semiconductor laser device comprising: including first and second laser units; each ~~unit~~ having a ridge type structure and including each ~~unit comprising~~ a multilayer structure ~~body~~ having an active layer, an n-type and p-type semiconductor layers sandwiching said active layer therebetween, made of at least an n-type semiconductor layer, an active layer and a p-type semiconductor layer deposited in this order, and a p-side electrode and an n-side electrode,

d wherein the ridge portions of said first and second laser units face each other at side surfaces of said ridge portion and the p-side electrode of the first laser unit is electrically connected to the n-side electrode of the second laser unit and the n-side electrode of the first laser unit is electrically connected to the p-side electrode of the second laser unit.

Add Limitations to Claim 1
Claim 2 (Previously Amended): The semiconductor laser device according to claim 1, further comprising:

a first connecting layer interconnecting said p-side electrode of the first laser unit and said n-side electrode of the second laser unit; and

a second connecting layer interconnecting between said p-side electrode of the second laser unit and said n-side electrode of the first laser unit.

Claim 3 (Original): The semiconductor laser device according to claim 2, wherein the first and second laser units are disposed in an opposing fashion with each other with an insulating layer interposed between the first and second laser units.

Claim 4 (Previously Amended): The semiconductor laser device according to claim 2, wherein at least one of said first and said second connecting layers has a Schottky barrier.

C. Carter
Claim 5 (Previously Amended): The semiconductor laser device according to claim 1, wherein at least one of the first and second laser units has a Schottky barrier between the p-side electrode and the p-type semiconductor layer.

Claim 6 (Previously Amended): The semiconductor laser device according to claim 1, wherein at least one of the first and second laser units is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.

Claims 7-10 (Withdrawn)

Claim 11 (Previously Added): The semiconductor laser device according to claim 3, wherein at least one of the connecting layers has a Schottky barrier.

Claim 12 (Previously Added): The semiconductor laser device according to claim 2, wherein at least one of the first laser unit and the second laser unit has a Schottky barrier between the p-side electrode and the p-type semiconductor layer.

Claim 13 (Previously Added): The semiconductor laser device according to claim 3, wherein at least one of the first laser unit and the second laser unit has a Schottky barrier between the p-side electrode and the p-type semiconductor layer.

Claim 14 (Previously Amended): The semiconductor laser device according to claim 2, wherein at least one of the first and second laser units is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.

Claim 15 (Previously Amended): The semiconductor laser device according to claim 3, wherein at least one of the first and second laser units is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.

Claim 16 (Currently Amended): The semiconductor laser device according to claim 4, wherein at least one of the first and second laser units is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.

Claim 17 (Previously Amended): The semiconductor laser device according to claim 5, wherein at least one of the first and second laser units is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.
